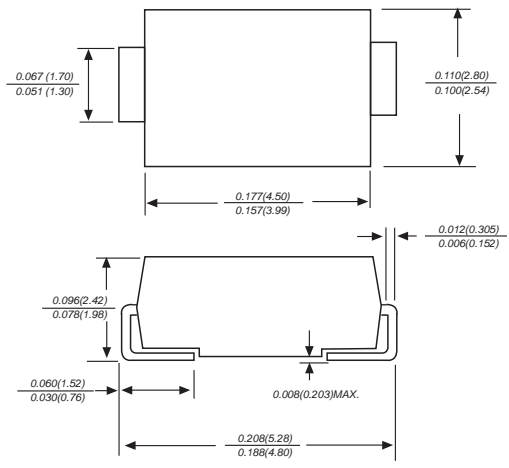


ES1A THRU ES1J

| | |
|---|---|
| <p style="text-align: center;">DO-214AC/SMA</p>  <p style="text-align: center; font-size: small;">Dimensions in inches and (millimeters)</p> | <p style="text-align: center;">FEATURES</p> <ul style="list-style-type: none"> ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0 ◆ For surface mounted applications ◆ Low reverse leakage ◆ Built-in strain relief, ideal for automated placement ◆ High forward surge current capability ◆ High temperature soldering guaranteed: 250°C/10 seconds at terminals ◆ Glass passivated chip junction |
| <p style="text-align: center;">MECHANICAL DATA</p> <p>Case: JEDEC DO-214AC molded plastic body over passivated chip Terminals: Solder plated, solderable per MIL-STD-750, Method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: 0.002 ounce, 0.07 grams</p> | |

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

| Catalog Number | SYMBOLS | ES1A | ES1B | ES1C | ES1D | ES1E | ES1G | ES1J | UNITS |
|---|-----------------|-------------|------|------|------|------|------|------|---------------------------|
| Maximum repetitive peak reverse voltage | V_{RRM} | 50 | 100 | 150 | 200 | 300 | 400 | 600 | VOLTS |
| Maximum RMS voltage | V_{RMS} | 35 | 70 | 105 | 140 | 210 | 280 | 420 | VOLTS |
| Maximum DC blocking voltage | V_{DC} | 50 | 100 | 150 | 200 | 300 | 400 | 600 | VOLTS |
| Maximum average forward rectified current at $T_L=55^\circ\text{C}$ | $I_{(AV)}$ | 1.0 | | | | | | | Amp |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | I_{FSM} | 30.0 | | | | | | | Amps |
| Maximum instantaneous forward voltage at 1.0A | V_F | 0.95 | | | 1.25 | | 1.7 | | Volts |
| Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$ | I_R | 5.0 50.0 | | | | | | | μA |
| Maximum reverse recovery time (NOTE 1) | t_{rr} | 35 | | | | | | | ns |
| Typical junction capacitance (NOTE 2) | C_J | 15.0 | | | | | | | pF |
| Typical thermal resistance (NOTE 3) | $R_{\theta JA}$ | 60.0 | | | | | | | $^\circ\text{C}/\text{W}$ |
| Operating junction and storage temperature range | T_J, T_{STG} | -50 to +150 | | | | | | | $^\circ\text{C}$ |

Note: 1. Reverse recovery condition $I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

ES1A THRU ES1J

